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Stocking Distributor

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[Vishay/Siliconix](#)
[TN0200K-T1-E3](#)

For any questions, you can email us directly:

sales@integrated-circuit.com

New Product



TN0200K
 Vishay Siliconix

N-Channel 20-V (D-S) MOSFETs

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
20	0.4 at V _{GS} = 4.5 V	0.73
	0.5 at V _{GS} = 2.5 V	0.65

FEATURES

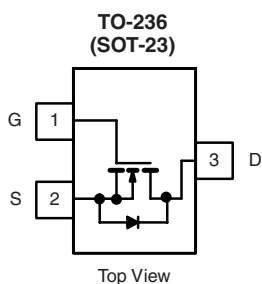
- TrenchFET® Power MOSFET
- ESD Protected: 4000 V



RoHS
 COMPLIANT

APPLICATIONS

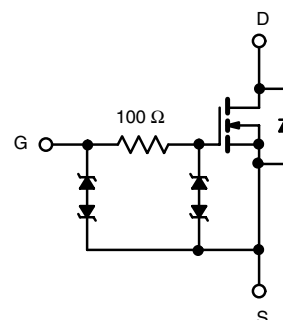
- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers
- Battery Operated Systems, DC/DC Converters
- Solid-State Relays
- Load/Power Switching-Cell Phones, Pagers



Marking Code: K2ywl

K2 = Part Number Code for TN0200K

y = Year Code
 w = Week Code
 l = Lot Traceability



Ordering Information: TN0200K-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	± 8	
Continuous Drain Current (T _J = 150 °C) ^b	I _D	T _A = 25 °C	A
		T _A = 70 °C	
Pulsed Drain Current ^a	I _{DM}	4	
Continuous Source Current (Diode Conduction) ^b	I _S	0.3	
Power Dissipation ^b	P _D	T _A = 25 °C	W
		T _A = 70 °C	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^b	R _{thJA}	357	°C/W

Notes:

- a. Pulse width limited by maximum junction temperature.
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.

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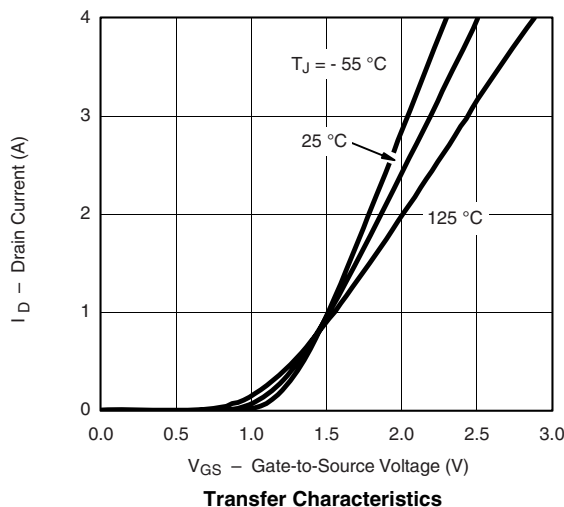
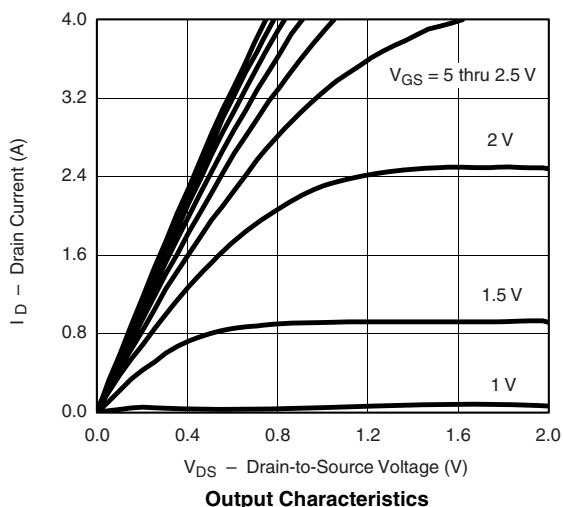
SPECIFICATIONS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 10\text{ }\mu\text{A}$	20			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 50\text{ }\mu\text{A}$	0.45	0.6	1.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$			± 5	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$ $T_J = 55\text{ }^\circ\text{C}$			0.1 10	μA
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$	2.5			A
		$V_{DS} \geq 5\text{ V}, V_{GS} = 2.5\text{ V}$	1.5			
Drain-Source On-Resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 0.6\text{ A}$		0.2	0.4	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 0.6\text{ A}$		0.25	0.5	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 5\text{ V}, I_D = 0.6\text{ A}$		2.2		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 0.3\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}$ $I_D = 0.6\text{ A}$		1400	2000	pC
Gate-Source Charge	Q_{gs}			190		
Gate-Drain Charge	Q_{gd}			300		
Gate Resistance	R_g			105		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 16\text{ }\Omega$ $I_D \cong 0.6\text{ A}, V_{GEN} = 4.5\text{ V}$ $R_g = 6\text{ }\Omega$		17	25	ns
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			55	85	
Fall Time	t_f			30	45	

Notes:

- a. Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted

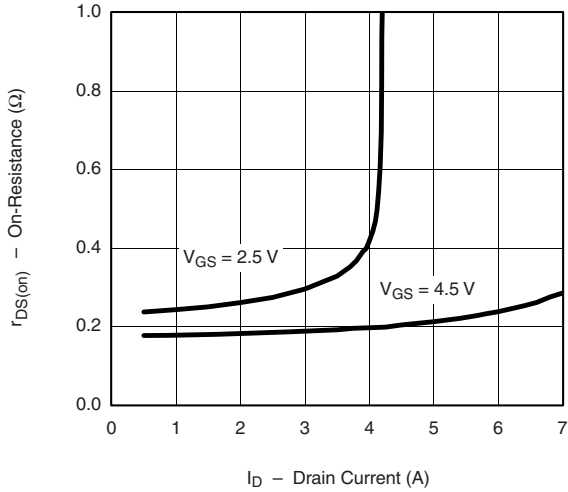


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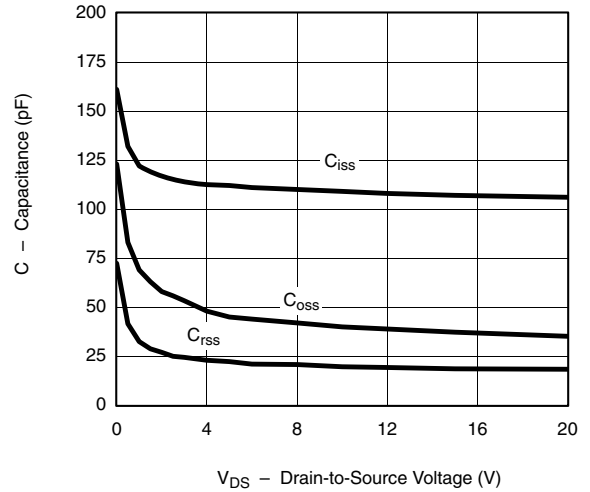


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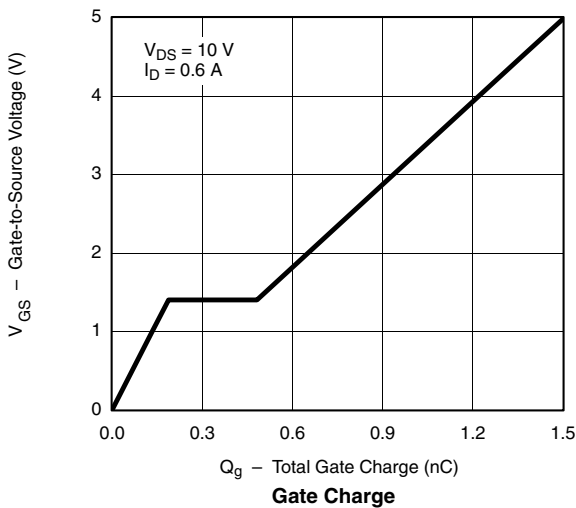
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



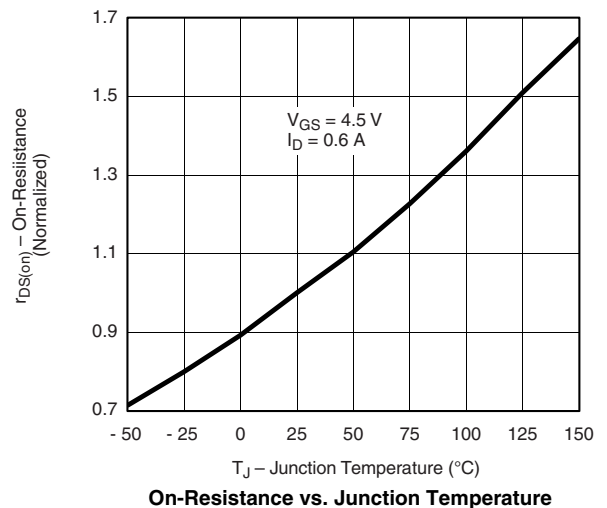
On-Resistance vs. Drain Current



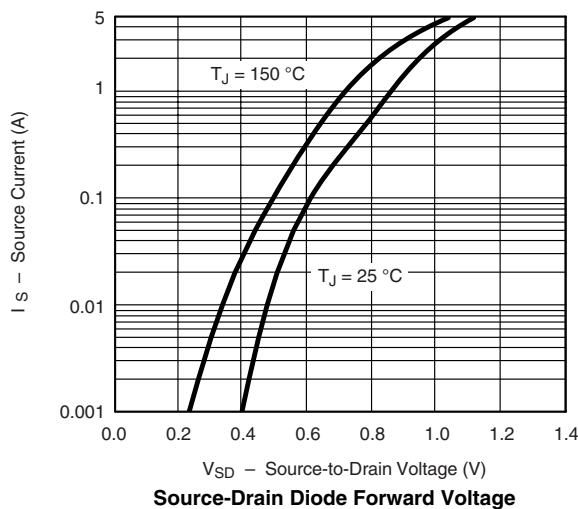
Capacitance



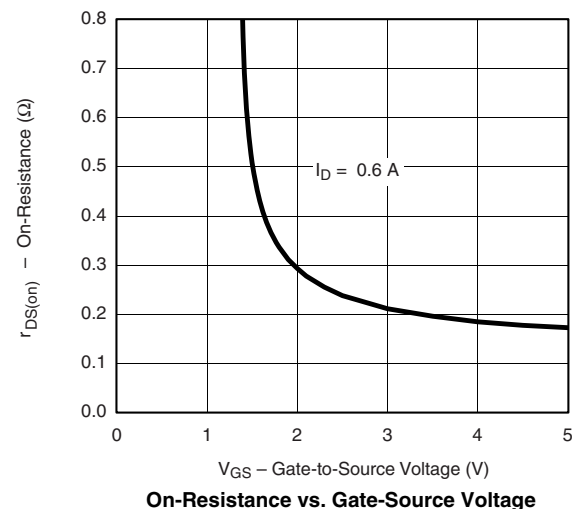
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-Source Voltage

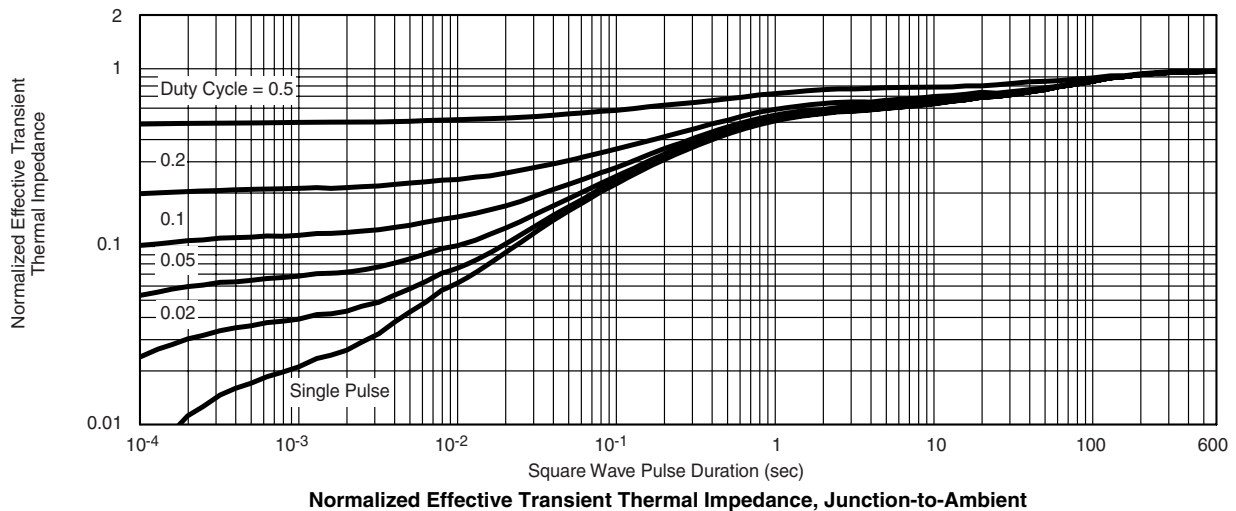
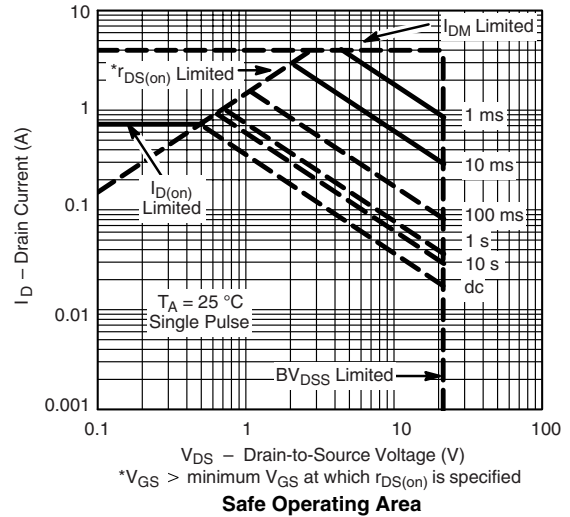
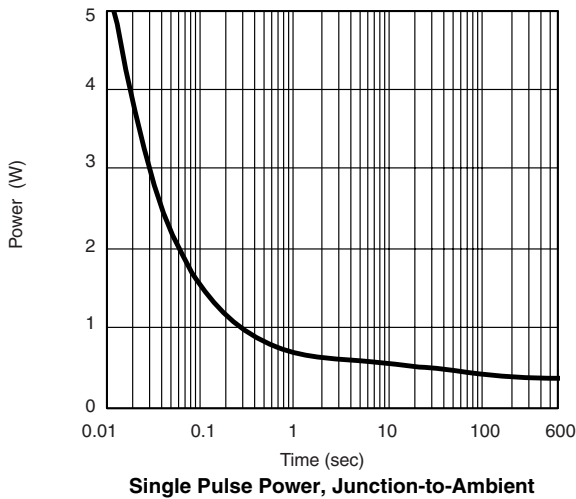
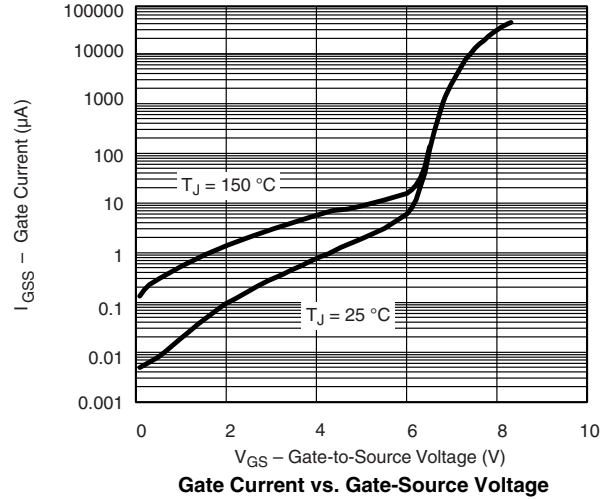
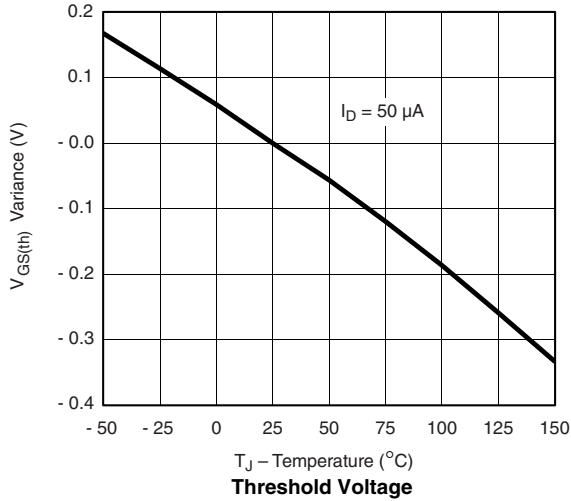
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?72678>.



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Vishay

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